IN THE CLAIMS:

Please amend claims 7, 11, 14, and 15, as follows:

1-6.   (Previously Cancelled)

7.   (Presently Amended)   A method for making a high fill factor image array comprising the steps:

providing a plurality of source-drain metal contacts;

depositing a first passivation layer;

depositing a second passivation layer that suppresses lateral leakage current;

opening a plurality of via holes through the first and second passivation layers;

depositing a layer of conductive material;

depositing a first doped a-Si layer;

patterning to form [the] collection electrodes;

depositing a continuous layer of i a-Si;

depositing a continuous second layer of doped a-Si;

depositing and patterning an upper conductive layer.

8.   (Original)   The method for making a high fill factor image array according to claim 7, wherein the first passivation layer comprises silicon oxynitride, BCB, or a polyamide.

9.   (Original)   The method for making a high fill factor image array according to claim 7, wherein the second passivation layer is an oxide.

10. (Original) The method for making a high fill factor image array according to claim 7, wherein the second has a thickness of about 1000 Å.

11. (Presently Amended) A high fill factor image array formed by:

providing a plurality of source-drain metal contacts;

depositing a first passivation layer;

depositing a second passivation layer over the first passivation layer that suppresses lateral leakage current;

opening a plurality of via holes through the first and second passivation layers;

depositing a layer of conductive material;

depositing a first doped a-Si layer;

patterning to form [the] collection electrodes;

depositing a continuous layer of i a-Si;

depositing a continuous second layer of doped a-Si;

depositing and patterning an upper conductive layer.

12. (Original) The high fill factor image array of claim 11, wherein the first passivation layer comprises at least one of silicon oxynitride, BCB, or a polyamide.

13. (Original) The high fill factor image array of claim 11, wherein the second passivation layer is an oxide.

14. (Presently Amended) The high fill factor image array of claim 11, wherein the second <u>passivation layer</u> has a thickness of about 1000 Å.

15. (Presently Amended) The high fill factor image array of claim 11, wherein <u>a</u> [the wherein the] thickness of the second passivation layer is less than <u>a</u> [the] thickness of the first passivation layer.